



SiC Bridge Rectifier

SKM125KD12SC

Features*

- Full Silicon Carbide (SiC) power module
- 1200V SiC Schottky FWDs
- High frequency rectifier
- Improved thermal performances with Aluminium Nitride (AlN) substrate
- UL recognized, file no. E63532

Typical Applications

- Rectifiers for DC/DC converters
- High frequency rectifier applications

Remarks

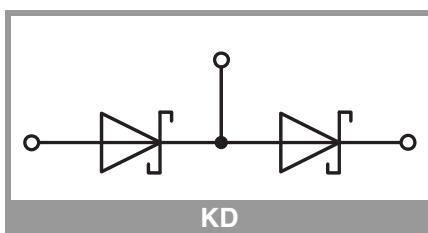
- Case temperature limited to $T_C=125^\circ\text{C}$
- Recommended $T_{jop} = -40\ldots+150^\circ\text{C}$

Absolute Maximum Ratings		Values	Unit
Symbol	Conditions		
Diode 1			
V_{RRM}	$T_j = 25^\circ\text{C}$	1200	V
I_F	$T_j = 175^\circ\text{C}$	264	A
	$T_c = 25^\circ\text{C}$	200	A
I_{Fnom}	$T_c = 80^\circ\text{C}$	180	A
I_{FSM}	10 ms, sin 180°, $T_j = 150^\circ\text{C}$	630	A
i^2t	10 ms, sin 180°, $T_j = 150^\circ\text{C}$	1984	A^2s
T_j		-40 ... 175	$^\circ\text{C}$

Absolute Maximum Ratings		Values	Unit
Symbol	Conditions		
Module			
$I_{t(\text{RMS})}$		500	A
T_{stg}	module without TIM	-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, $t = 1 \text{ min}$	4000	V

Characteristics		min.	typ.	max.	Unit
Symbol	Conditions				
Diode 1					
V_F	$I_F = 180 \text{ A}$	$T_j = 25^\circ\text{C}$	1.36	1.55	V
	chiplevel	$T_j = 150^\circ\text{C}$	1.70	1.98	V
V_{FO}	chiplevel	$T_j = 25^\circ\text{C}$	0.95	1.05	V
		$T_j = 150^\circ\text{C}$	0.80	0.90	V
r_F	chiplevel	$T_j = 25^\circ\text{C}$	2.3	2.8	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	5.0	6.0	$\text{m}\Omega$
C_j	$V_R = 800 \text{ V}, f = 1 \text{ MHz}, T_j = 25^\circ\text{C}$		0.840		nF
Q_c	$V_R = 800 \text{ V}, di/dt_{\text{off}} = 500 \text{ A}/\mu\text{s}, T_j = 25^\circ\text{C}$		0.67		μC
$R_{\text{th(j-c)}}$	per diode			0.215	K/W

Characteristics		min.	typ.	max.	Unit
Symbol	Conditions				
Module					
L_{CE}		15			nH
$R_{\text{CC+EE'}}$	measured per switch	$T_C = 25^\circ\text{C}$	0.55		$\text{m}\Omega$
		$T_C = 125^\circ\text{C}$	0.85		$\text{m}\Omega$
$R_{\text{th(c-s)}}$	calculated without thermal coupling ($\lambda_{\text{grease}}=0.81 \text{ W}/(\text{m}^*\text{K})$)		0.02	0.038	K/W
M_s	to heat sink M6	3	5		Nm
M_t	to terminals M6	2.5	5		Nm
w				325	g



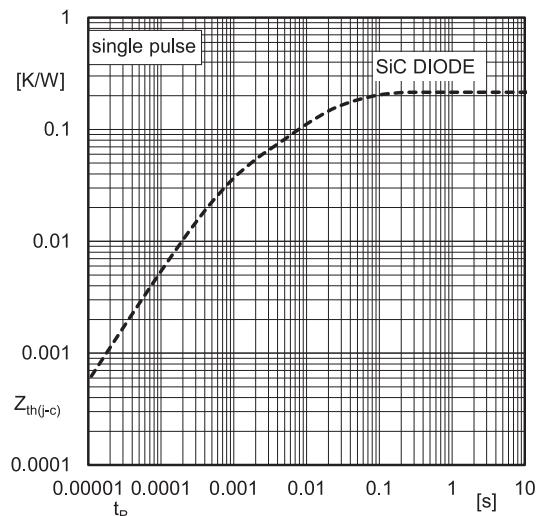


Fig. 9: Typ. transient thermal impedance

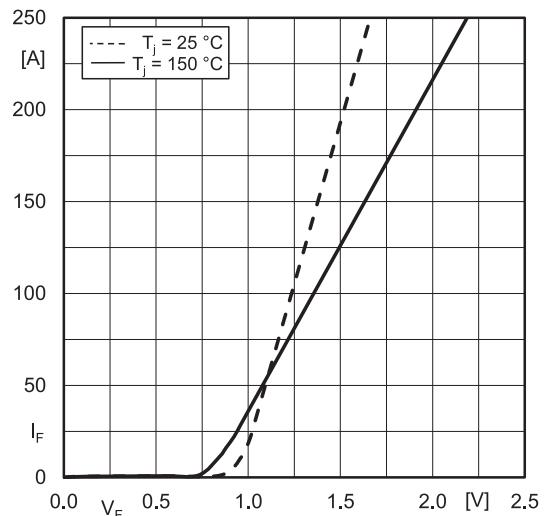


Fig. 10: Typ. Diode forward charact., incl. $R_{CC} + EE'$

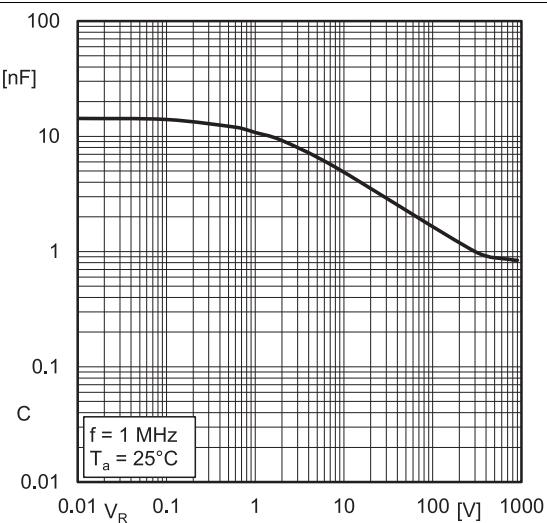
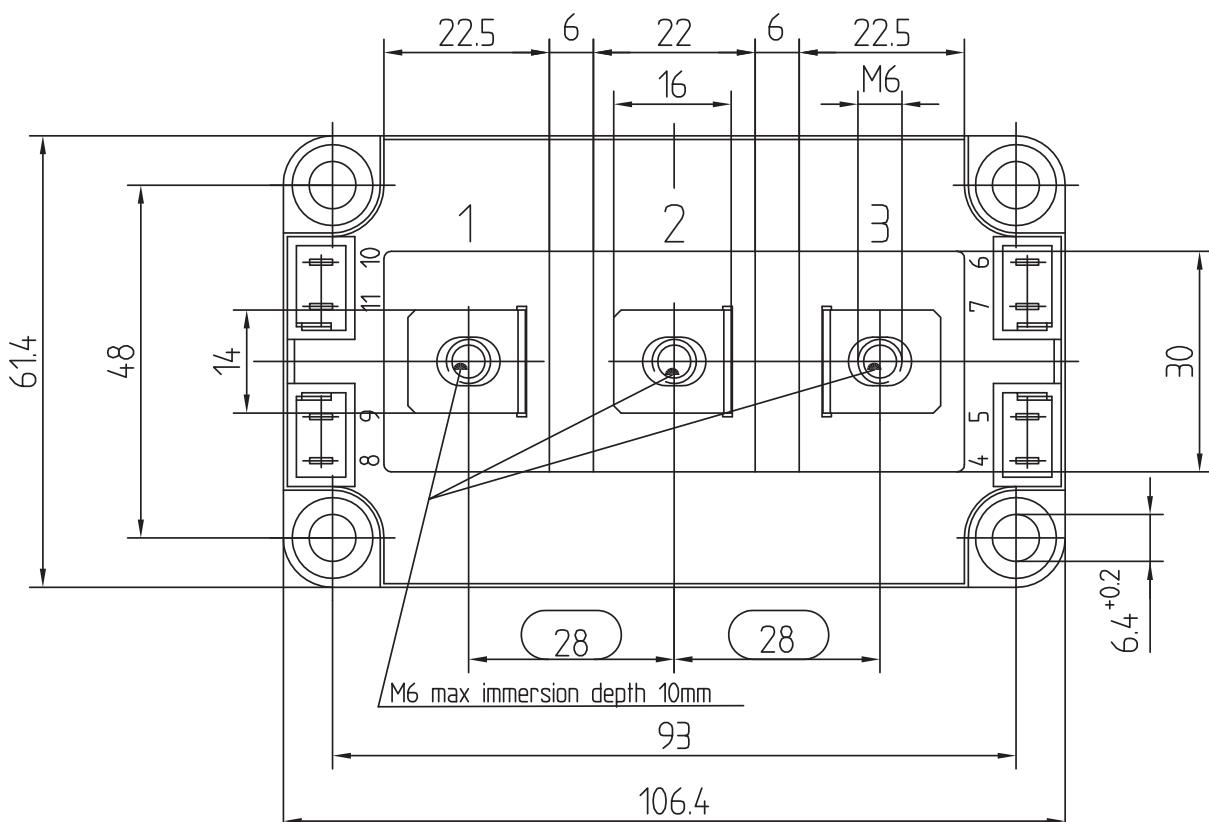
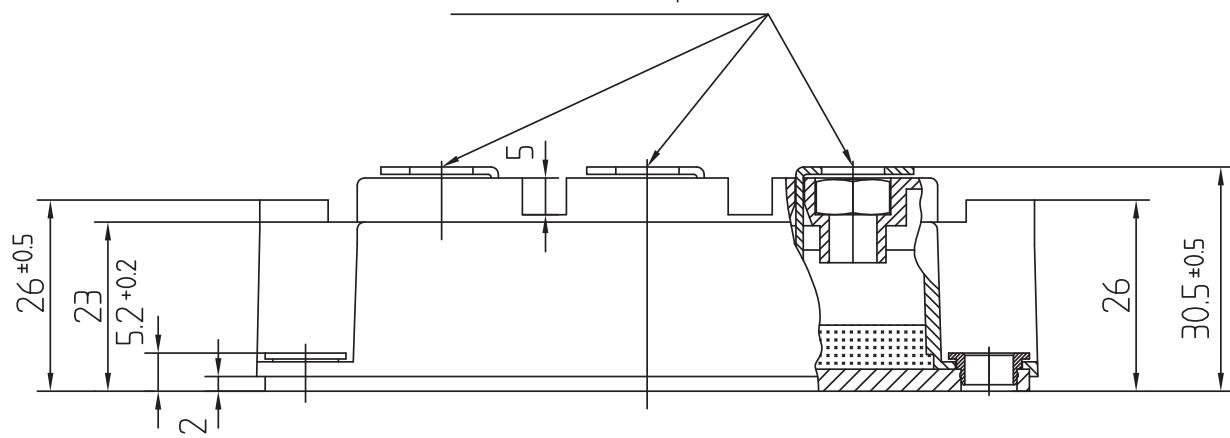


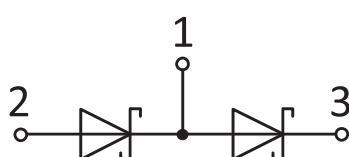
Fig. 20: Typ. Capacitance-voltage characteristic

Dimension in mm

M6 max immersion depth 10mm



SEMITRANS 3



KD

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

***IMPORTANT INFORMATION AND WARNINGS**

The specifications of SEMIKRON products may not be considered as guarantee or assurance of product characteristics ("Beschaffenheitsgarantie"). The specifications of SEMIKRON products describe only the usual characteristics of products to be expected in typical applications, which may still vary depending on the specific application. Therefore, products must be tested for the respective application in advance. Application adjustments may be necessary. The user of SEMIKRON products is responsible for the safety of their applications embedding SEMIKRON products and must take adequate safety measures to prevent the applications from causing a physical injury, fire or other problem if any of SEMIKRON products become faulty. The user is responsible to make sure that the application design is compliant with all applicable laws, regulations, norms and standards. Except as otherwise explicitly approved by SEMIKRON in a written document signed by authorized representatives of SEMIKRON, SEMIKRON products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury. No representation or warranty is given and no liability is assumed with respect to the accuracy, completeness and/or use of any information herein, including without limitation, warranties of non-infringement of intellectual property rights of any third party. SEMIKRON does not assume any liability arising out of the applications or use of any product; neither does it convey any license under its patent rights, copyrights, trade secrets or other intellectual property rights, nor the rights of others. SEMIKRON makes no representation or warranty of non-infringement or alleged non-infringement of intellectual property rights of any third party which may arise from applications. Due to technical requirements our products may contain dangerous substances. For information on the types in question please contact the nearest SEMIKRON sales office. This document supersedes and replaces all information previously supplied and may be superseded by updates. SEMIKRON reserves the right to make changes.